

Graphene Film Growth on Silicon Carbide by Hot Filament Chemical Vapor Deposition

Sandra Rodríguez-Villanueva, Frank Mendoza, Brad R. Weiner and Gerardo Morell

Supplementary information

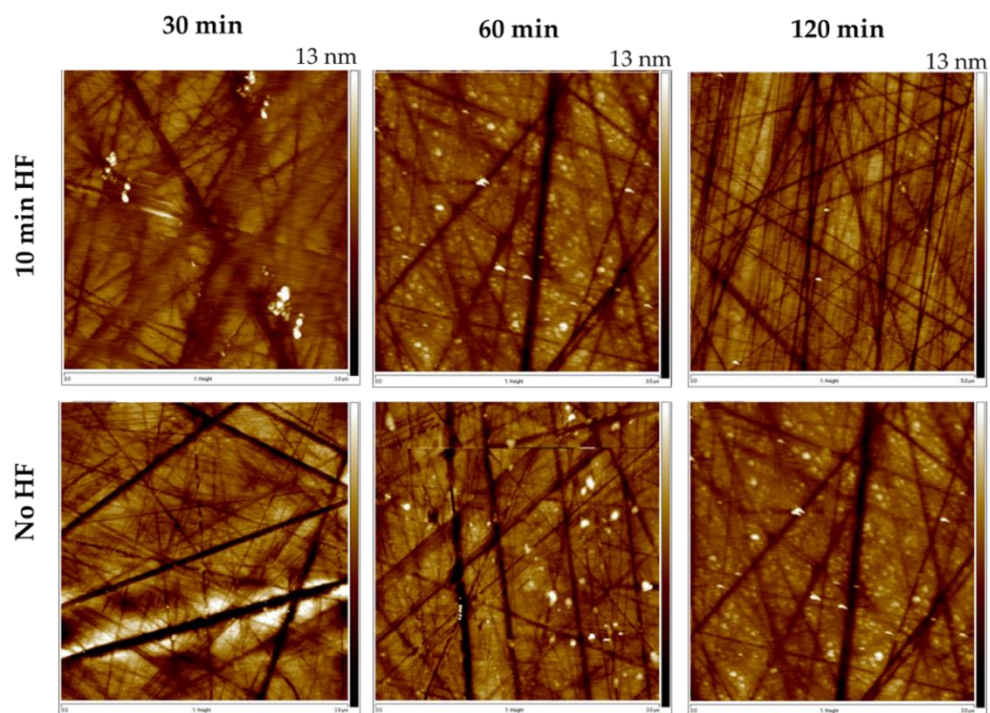


Figure S1. AFM measurements of SiC substrates cleaned and uncleaned at different annealing time (30, 60 and 120 minutes).